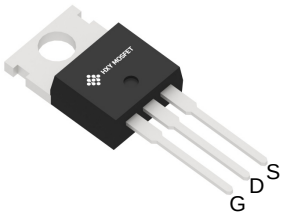
HUF75332P3

N-Channel Enhancement Mode MOSFET

Description

The HUF75332P3 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

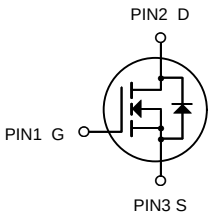


TO-220C

General Features

V_{DS} =60V,I_D =60A

$R_{DS(ON)}$ < 20mΩ @ V_{GS}=10V



N-Channel MOSFET

Application

High efficiency switch mode power supplies

Power factor correction

Electronic lamp ballast

Package Marking and Ordering Information

Product ID	Pack	Brand	Units Tube
HUF75332P3	TO-220C	HXY MOSFET	50

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	60	V
VGS	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Drain Current	60	A
IDM	Pulsed Drain Current[1]	240	A
P_D@T_C=25°C	Total Power Dissipation	120	W
TSTG	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Electrical Characteristics (T_C=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage (Note 1)	BV_{DSS}	V_{GS}=0V I_D=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	60	68	-	nA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.0	-	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=25A	-	17	20	mΩ
Forward Transconductance	g_{FS}	V_{DS}=30V,I_D=40A	15	-	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0V , F=1.0MHz	-	4050	-	PF
Output Capacitance	C_{oss}		-	430	-	PF
Reverse Transfer Capacitance	C_{rss}		-	110	-	PF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V,I_D=40A R_G=50Ω (Note 2)	-	60	-	nS
Turn-on Rise Time	t_r		-	185	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	75	-	nS
Turn-Off Fall Time	t_f		-	60	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=40A, V_{GS}=10V (Note 2)	-	39	-	nC
Gate-Source Charge	Q_{gs}		-	9.3	-	nC
Gate-Drain Charge	Q_{gd}		-	13	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=60A	-		1.5	V
Diode Forward Current (Note 2)	I_S		-	-	60	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

Typical Electrical

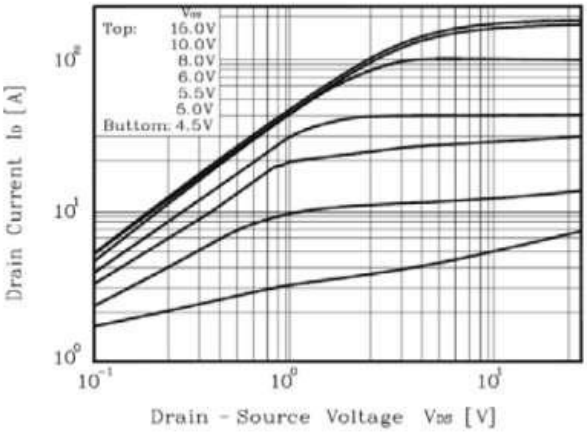


Figure 1. On Region Characteristics

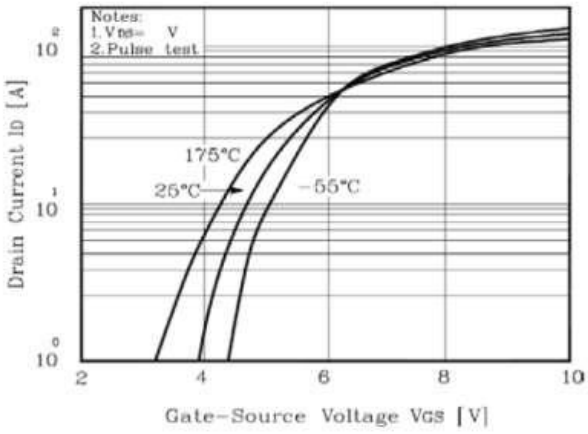


Figure 2. Transfer Characteristics

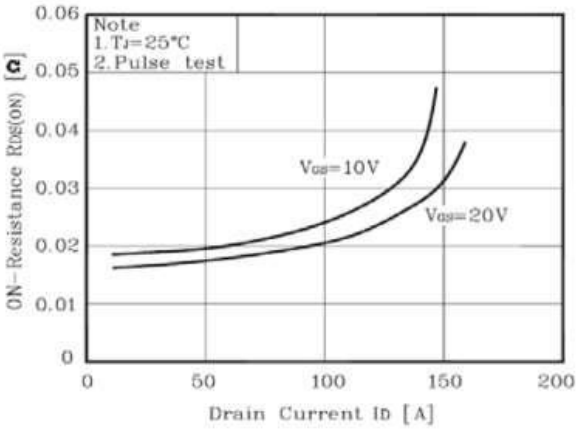


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

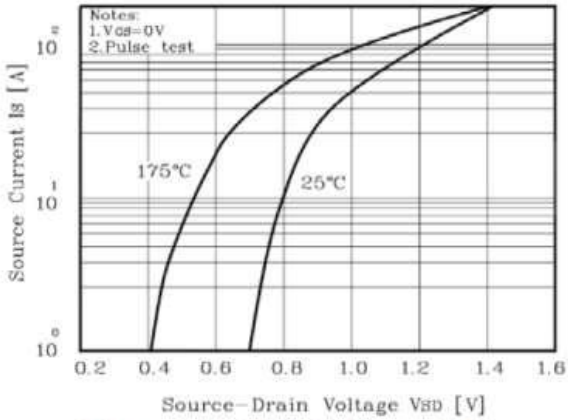


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

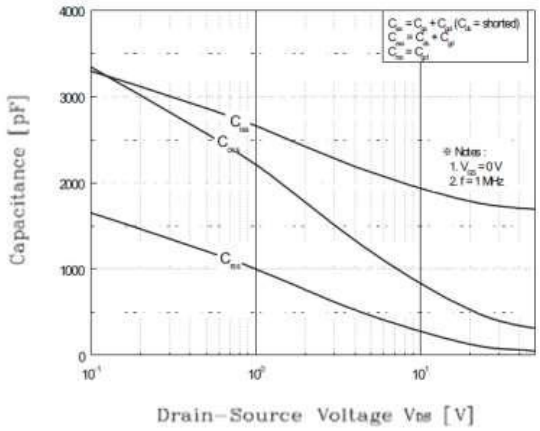


Figure 5. Capacitance Characteristics

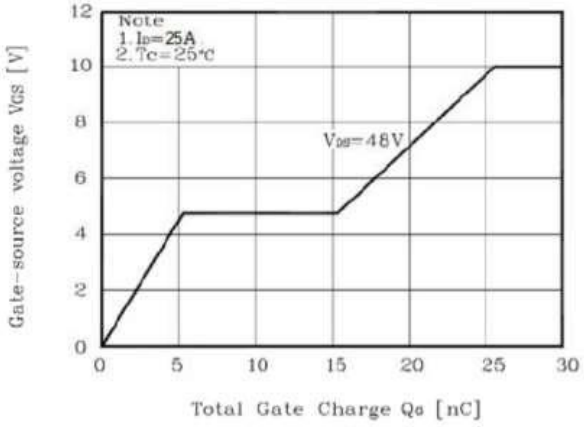


Figure 6. Gate Charge Characteristics

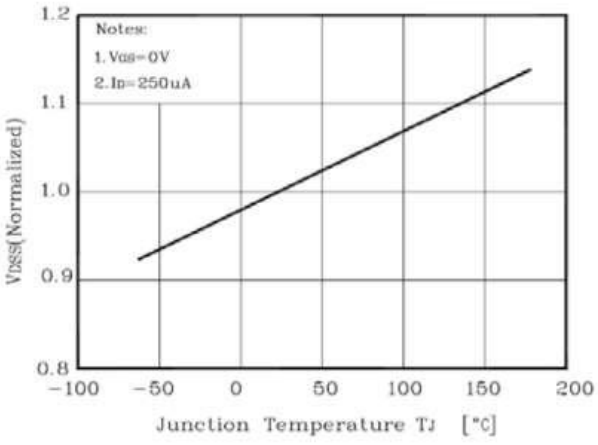


Figure 7. Breakdown Voltage Variation vs Temperature

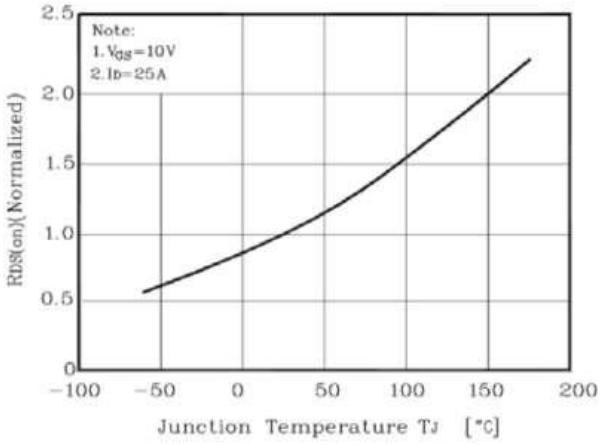


Figure 8. On-Resistance Variation vs Temperature

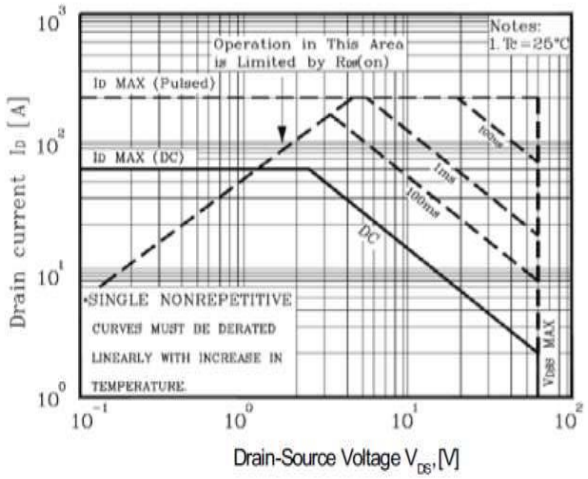


Figure 9. Maximum Safe Operating Area

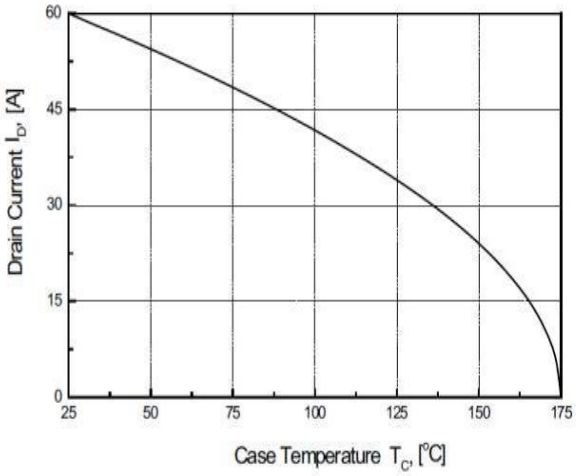


Figure 10. Maximum Drain Current vs Case Temperature

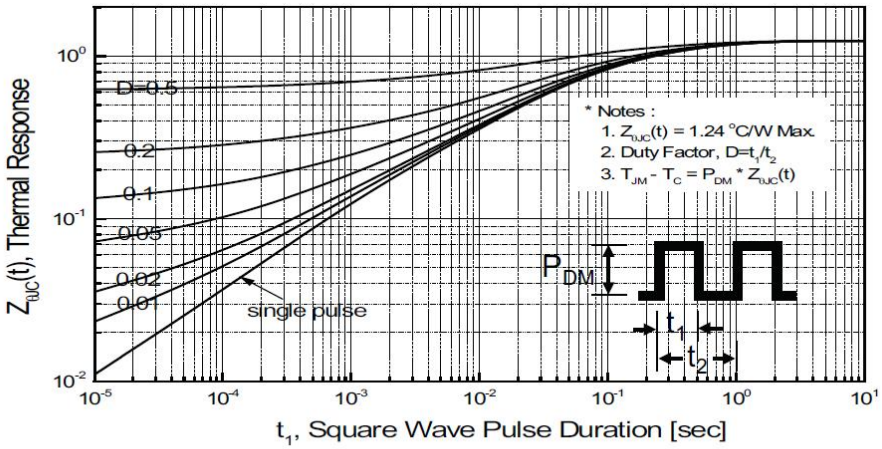
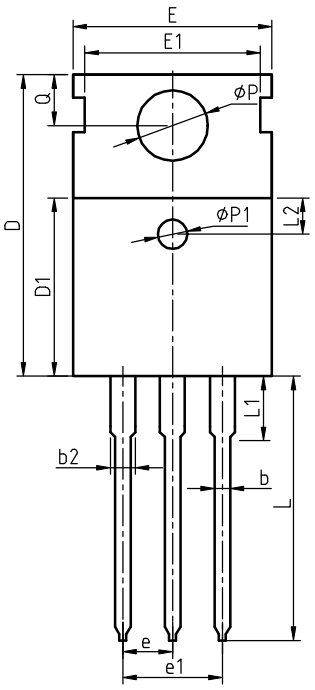
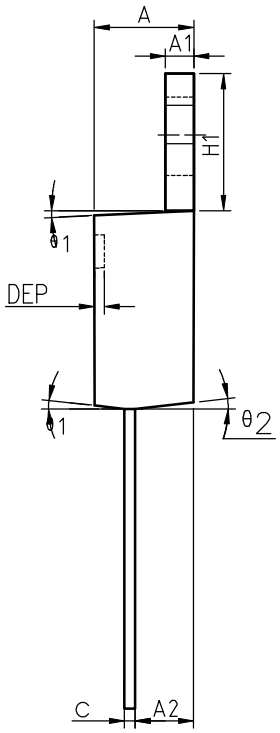
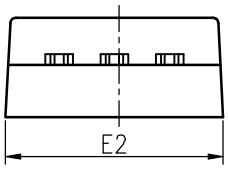


Figure 11. Transient Thermal Response Curve

Package Information
TO-220C







COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ1	5°	7°	9°	5°	7°	9°
θ2	1°	3°	5°	1°	3°	5°
θ3	1°	3°	5°	1°	3°	5°

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HC3D10170A HESDNC5VB1AF-B MAX487ESA SD15C SQJA04EP-T1_BE3 SS510C SS5150B
HC4D20120A IRLML6246PBF P6SMB36CA PESD5V0S1BB TPSMB100CA-VR HAD8542ARZ
HOPA2340UA HXY2101EI SS1045 US2M DTC143ZE HT7150 HXY2300MI P6SMB33CA HXY8205ES